

NCE N-Channel Super Trench Power MOSFET



The NCEP02515K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

• V_{DS} =250V,I_D =15A

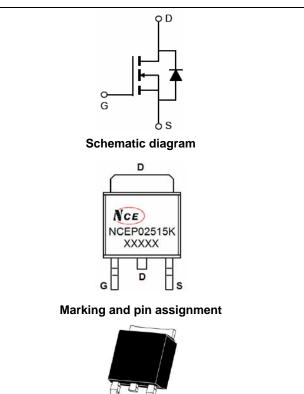
R_{DS(ON)}=200mΩ (typical) @ V_{GS}=10V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!



TO-252 -2Ltop view

Package Marking and Ordering Information

V	0	V			
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02515K	NCEP02515K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	250	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	ID	15	А
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	10.6	А
Pulsed Drain Current	I _{DM}	60	A
Maximum Power Dissipation	PD	140	W
Derating factor		0.93	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	80	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C

Thermal Characteristic

Thermal Résistance, Junction-to-Case ^(Note 2)	R _{eJC}	1.1	°C/W
	1,030	•••	0,



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	250	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I _D =15A	-	200	220	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =15A	15	-	-	S
Dynamic Characteristics (Note4)	· · ·		•			
Input Capacitance	C _{lss}		-	475		PF
Output Capacitance	C _{oss}	V _{DS} =125V,V _{GS} =0V, F=1.0MHz	-	34		PF
Reverse Transfer Capacitance	C _{rss}		-	1.2		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	4	-	nS
Turn-on Rise Time	tr	V _{DD} =125V, R∟=8Ω	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	10	-	nS
Turn-Off Fall Time	t _f		-	2	-	nS
Total Gate Charge	Qg		-	8.9	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =125V,I _D =15A,	-	3.3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =15A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	15	А
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-	25	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	110	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.

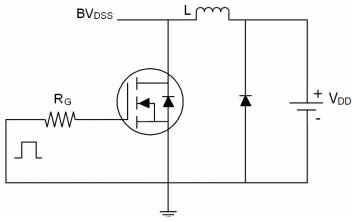
4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ \!\! \mathbb{C}$,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25\Omega

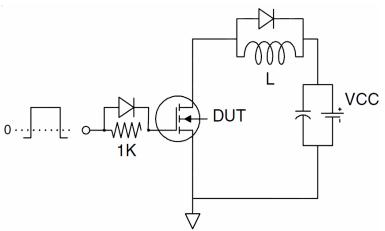


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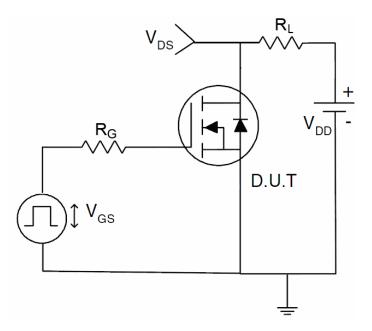
Test Circuit 1) E_{AS} test Circuit



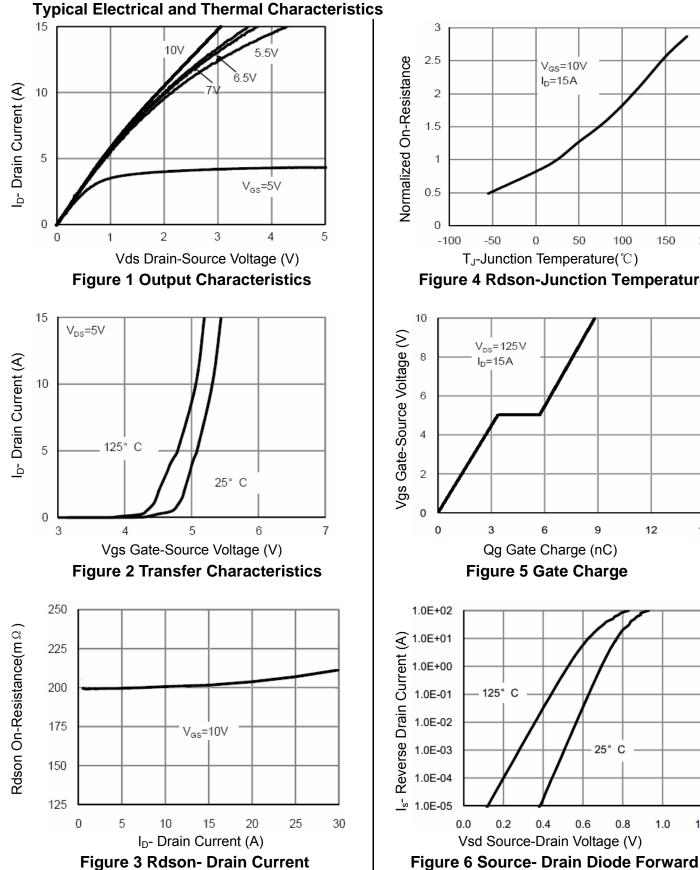
2) Gate charge test Circuit

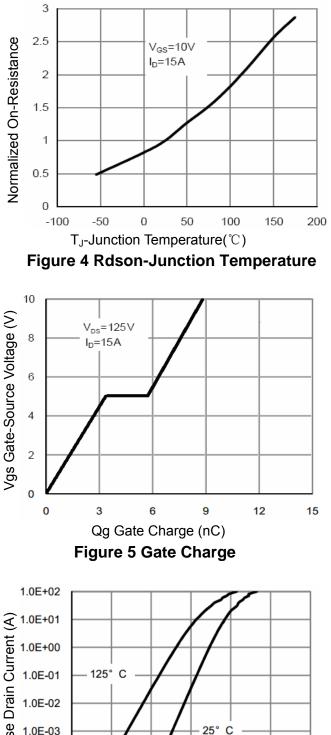


3) Switch Time Test Circuit









0.2

0.4

0.6

0.8

1.0

1.2



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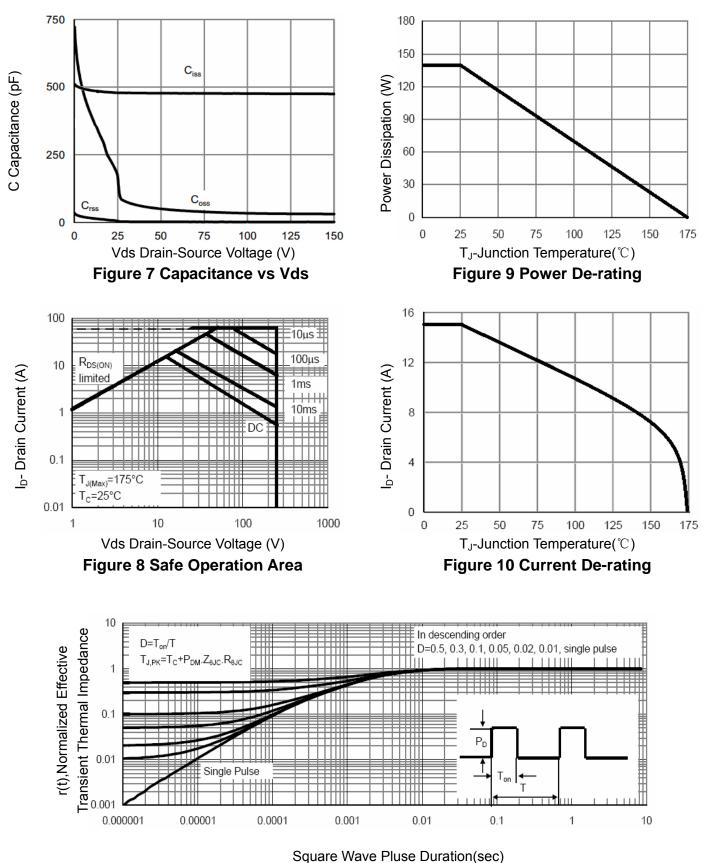
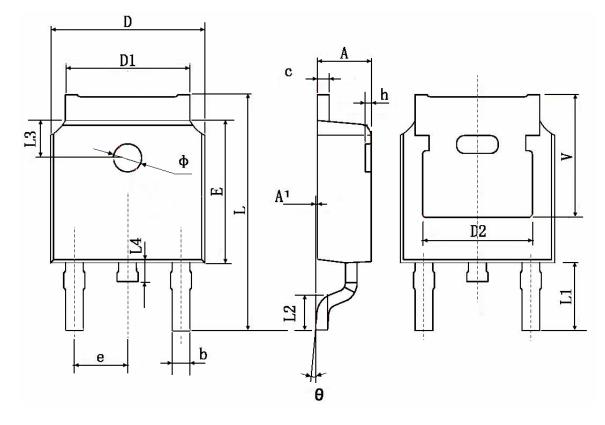


Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-252 Package Information



Querrale al	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.8	4.830 TYP. 0.190 TYP.			
E	6.000	6.200	0.236	0.244	
e	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350) TYP.	0.211 TYP.		



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